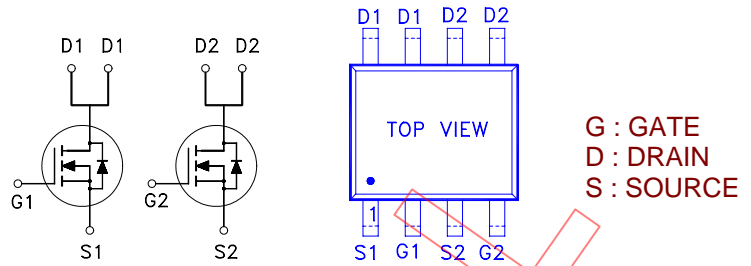


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
60	55m	4.5A



ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25\text{ }^\circ\text{C}$	I_D	4.5	A
	$T_C = 70\text{ }^\circ\text{C}$		4	
Pulsed Drain Current ¹		I_{DM}	20	
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	2	W
	$T_C = 70\text{ }^\circ\text{C}$		1.3	
Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		62.5	$^\circ\text{C} / \text{W}$

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

ELECTRICAL CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.0	1.5	2.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48V, V_{GS} = 0V$			1	μA
		$V_{DS} = 40V, V_{GS} = 0V, T_j = 55\text{ }^\circ\text{C}$			10	

On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 5V, V_{GS} = 10V$	20			A
Drain-Source Resistance ¹	On-State $R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 4A$		55	75	m
		$V_{GS} = 10V, I_D = 4.5A$		42	55	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 10V, I_D = 4.5A$		14		S

DYNAMIC							
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$			650	pF	
Output Capacitance	C_{oss}				80		
Reverse Transfer Capacitance	C_{rss}				35		
Total Gate Charge ²	Q_g	$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V,$ $I_D = 4.5A$			12.5	18	nC
Gate-Source Charge ²	Q_{gs}				2.4		
Gate-Drain Charge ²	Q_{gd}				2.6		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DD} = 30V$ $I_D = 1A, V_{GS} = 10V, R_{GEN} = 6$			11	20	nS
Rise Time ²	t_r				8	18	
Turn-Off Delay Time ²	$t_{d(off)}$				19	35	
Fall Time ²	t_f				6	15	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_c = 25 °C)

Continuous Current	I_S				1.3	A
Pulsed Current ³	I_{SM}				2.6	
Forward Voltage ¹	V_{SD}	$I_F = I_S A, V_{GS} = 0V$			1	V

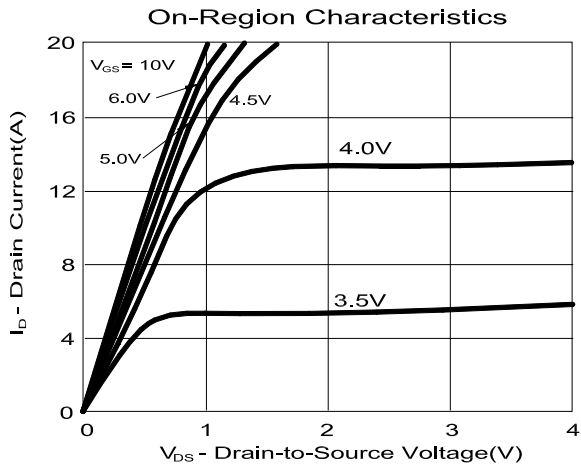
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

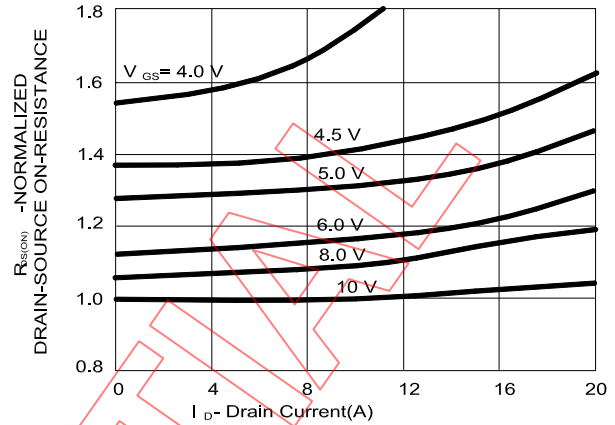
³Pulse width limited by maximum junction temperature.

REMARK: THE PRODUCT MARKED WITH "P5506HVG", DATE CODE or LOT #

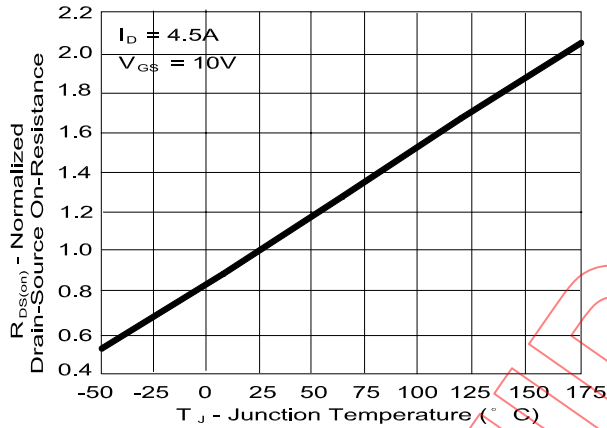
Orders for parts with Lead-Free plating can be placed using the PXXXXXXG parts name.



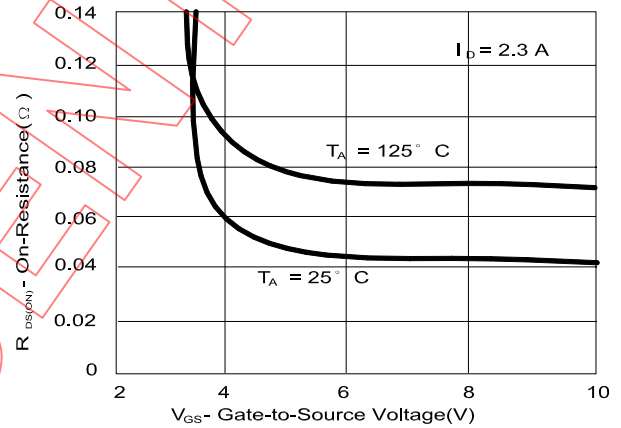
On-Resistance Variation with Drain Current and Gate Voltage



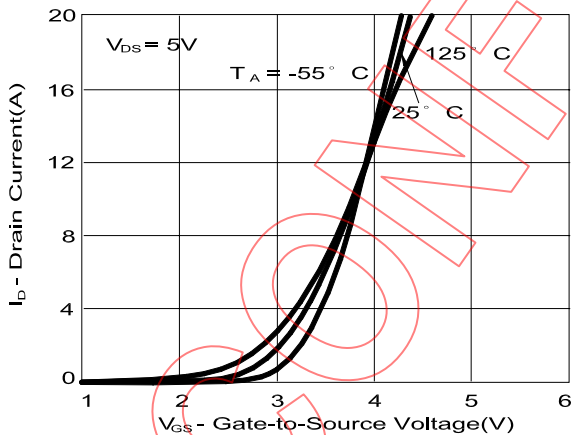
On-Resistance Variation with Temperature



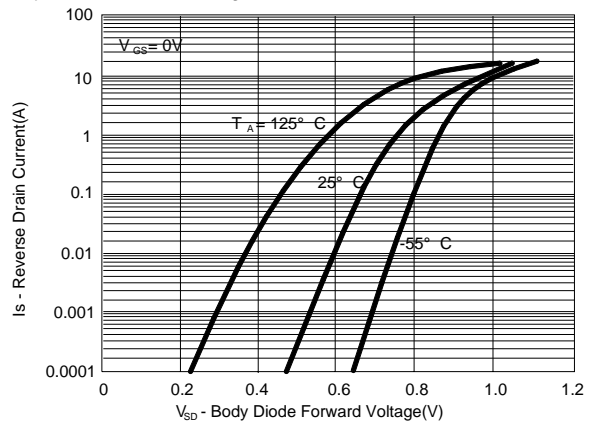
On-Resistance Variation with Gate-to-Source Voltage

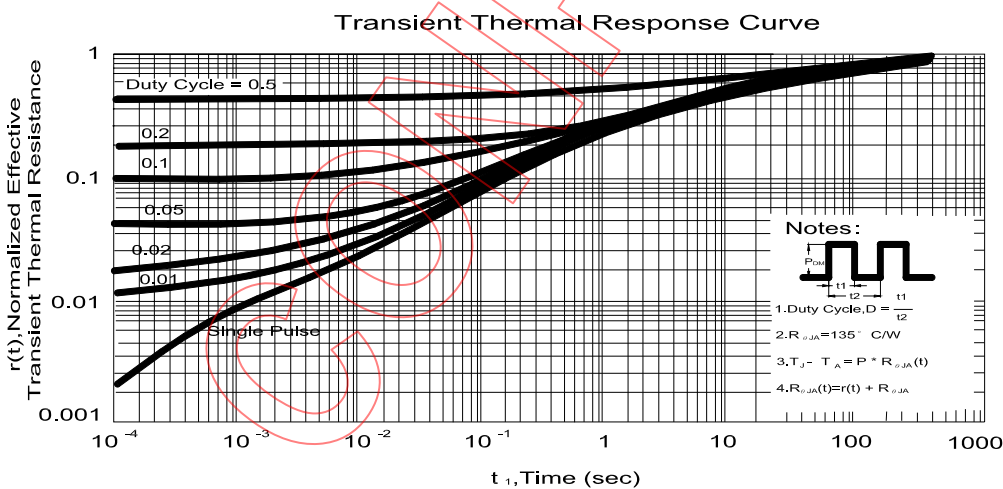
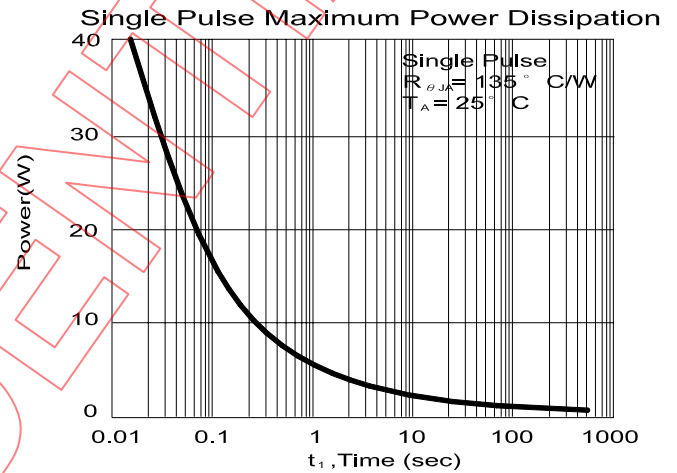
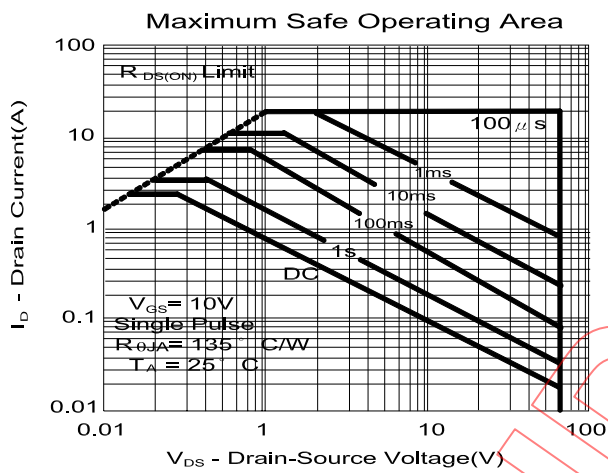
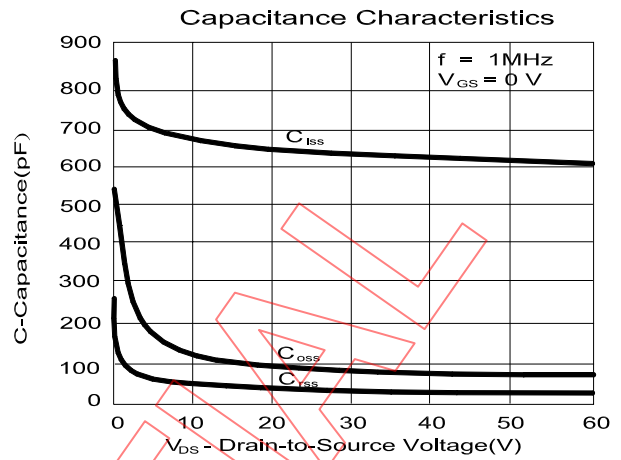
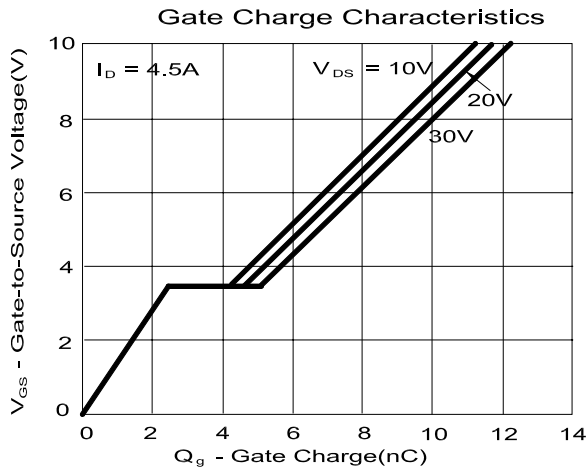


Transfer Characteristics



Body Diode Forward Voltage Variation with Source Current and Temperature





SOIC-8(D) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.5	0.715	0.83
B	3.8	3.9	4.0	I	0.18	0.254	0.25
C	5.8	6.0	6.2	J		0.22	
D	0.38	0.445	0.51	K	0°	4°	8°
E		1.27		L			
F	1.35	1.55	1.75	M			
G	0.1	0.175	0.25	N			

